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Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









IGBT

FMG2G300US60

Molding Type Module

General Description

Fairchild IGBT Power Module provides low conduction and switching losses as well as short circuit ruggedness. It's designed for the applications such as motor control, uninterrupted power supplies (UPS) and general inverters where short-circuit ruggedness is required.

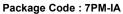
Features

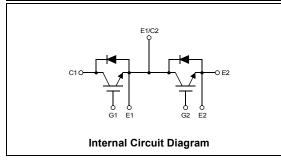
- Short Circuit Rated Time; 10us @ $T_C = 100$ °C, $V_{GE} = 15V$
- · High Speed Switching
- Low Saturation Voltage: V_{CE}(sat) = 2.1 V @ I_C = 300A
- · High Input Impedance
- · Fast & Soft Anti-Parallel FWD
- UL Certified No.E209204

Application

- AC & DC Motor Controls
- · General Purpose Inverters
- Robotics
- · Servo Controls
- UPS







Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Description		FMG2G300US60	Units
V _{CES}	Collector-Emitter Voltage		600	V
V _{GES}	Gate-Emitter Voltage		± 20	V
I _C	Collector Current	@ T _C = 80°C	300	Α
I _{CM (1)}	Pulsed Collector Current		600	Α
I _F	Diode Continuous Forward Current	@ T _C = 80°C	300	Α
I _{FM}	Diode Maximum Forward Current		600	Α
P _D	Maximum Power Dissipation	@ T _C = 25°C	892	W
T _{SC}	Short Circuit Withstand Time	@ T _C = 100°C	10	us
T _J	Operating Junction Temperature		-40 to +150	°C
T _{STG}	Storage Temperature Range		-40 to +125	°C
V _{ISO}	Isolation Voltage	@ AC 1minute	2500	V
Mounting Torque	Power Terminal Screw : M6		4.0	N.m
Mounting Torque	Mounting Screw : M6		4.0	N.m

Notes

(1) Repetitive rating: Pulse width limited by max. junction temperature

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Off Cha	racteristics					
BV _{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_{C} = 250uA$	600			V
ΔB _{VCES} / ΔΤ _J	Temperature Coeff. of Breakdown Voltage	V _{GE} = 0V, I _C = 1mA		0.6		V/°C
I _{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$			250	uA
I _{GES}	Gate - Emitter Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$			± 100	nA

V _{GE(th)}	Gate - Emitter Threshold Voltage	I_C =300mA, V_{CE} = V_{GE}	5.0	6.5	8.5	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	$I_C = 300A$, $V_{GE} = 15V$		2.1	2.7	V

Switching Characteristics

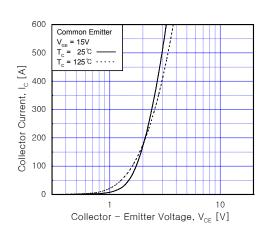
t _{d(on)}	Turn-On Delay Time			140		ns
t _r	Rise Time	V 000 V I 000 A		150		ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 300 \text{ V}, I_C = 300 \text{A},$		180		ns
t _f E _{on}	Fall Time	$R_G = 2Ω$, $V_{GE} = 15V$, Inductive Load, $T_C = 25°C$		140	250	ns
E _{on}	Turn-On Switching Loss	inductive Load, 1 _C = 25 C		4.4		mJ
E _{off}	Turn-Off Switching Loss			12		mJ
t _{d(on)}	Turn-On Delay Time			280		ns
t _r	Rise Time	\/ 000\/ L 000A		190		ns
$t_{d(off)}$	Turn-Off Delay Time	$V_{CC} = 300 \text{ V, } I_C = 300 \text{A,}$		250		ns
t _f	Fall Time	$R_G = 2\Omega$, $V_{GE} = 15V$, Inductive Load, $T_C = 125$ °C		230		ns
t _f E _{on}	Turn-On Switching Loss	inductive Load, T _C = 123 O		8.2		mJ
E _{off}	Turn-Off Switching Loss			19		mJ
T _{sc}	Short Circuit Withstand Time	$V_{CC} = 300 \text{ V}, V_{GE} = 15\text{V}$ @ $T_{C} = 100^{\circ}\text{C}$	10			us
Q_g	Total Gate Charge			990		nC
Q _{qe}	Gate-Emitter Charge	$V_{CE} = 300 \text{ V}, I_{C} = 300 \text{ A},$		210		nC
Q _{ge} Q _{gc}	Gate-Collector Charge	V _{GE} = 15V		350		nC

Electrical Characteristics of DIODE $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Units
V _{FM} Diode	Diode Forward Voltage I _F = 300A	1 = 2004	T _C = 25°C		1.9	2.8	\/
		IF - 300A	T _C = 100°C		1.8		v
h Diada Davierra Dasavierri Tirra		T _C = 25°C		90	130	no	
t _{rr}	Diode Reverse Recovery Time		T _C = 100°C		130		ns
	Diode Peak Reverse Recovery	I _F = 300A	T _C = 25°C		32	42	Α
'rr	Current	Current $\frac{di}{dt} = 600 \text{ A/us}$ $T_C = 10$	T _C = 100°C		63		A
Q _{rr}	Diode Reverse Recovery Charge	Diada Dayaraa Daaayary Charga	T _C = 25°C		1440	2700	nC
			T _C = 100°C		4095		nC

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JC}$	Junction-to-Case (IGBT Part, per 1/2 Module)		0.14	°C/W
$R_{\theta JC}$	Junction-to-Case (DIODE Part, per 1/2 Module)		0.22	°C/W
$R_{\theta JC}$	Case-to-Sink (Conductive grease applied)	0.035		°C/W
Weight	Weight of Module	360		g



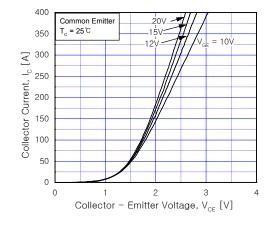
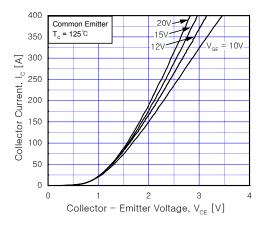


Fig 1. Typical Output Characteristics

Fig 2. Typical Saturation Voltage Characteristics



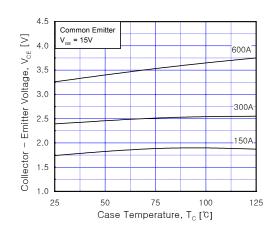
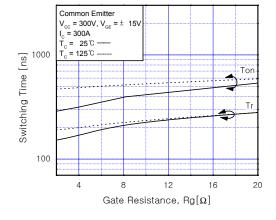


Fig 3. Typical Saturation Voltage Characteristics

Fig 4. Saturation Voltage vs. Case
Temperature at Variant Current Level



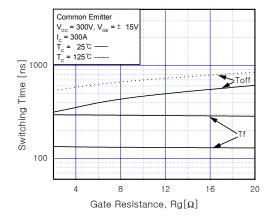


Fig 5. Turn-On Characteristics vs. Gate Resistance

Fig 6. Turn-Off Characteristics vs.
Gate Resistance

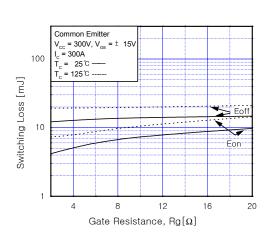


Fig 7. Switching Loss vs. Gate Resistance

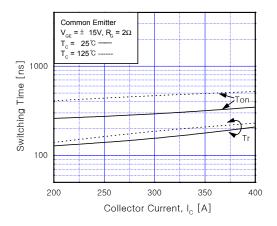


Fig 8. Turn-On Characteristics vs. Collector Current

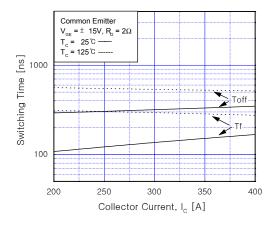


Fig 9. Turn-Off Characteristics vs. Collector Current

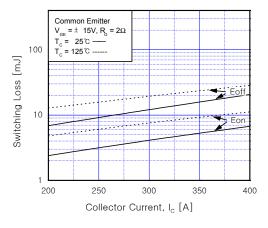


Fig 10. Switching Loss vs. Collector Current

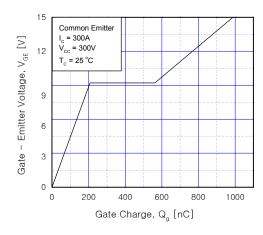


Fig 11. Gate Charge Characteristics

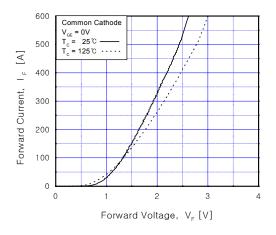


Fig 12. Forward Characteristics(diode)

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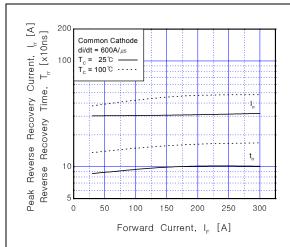
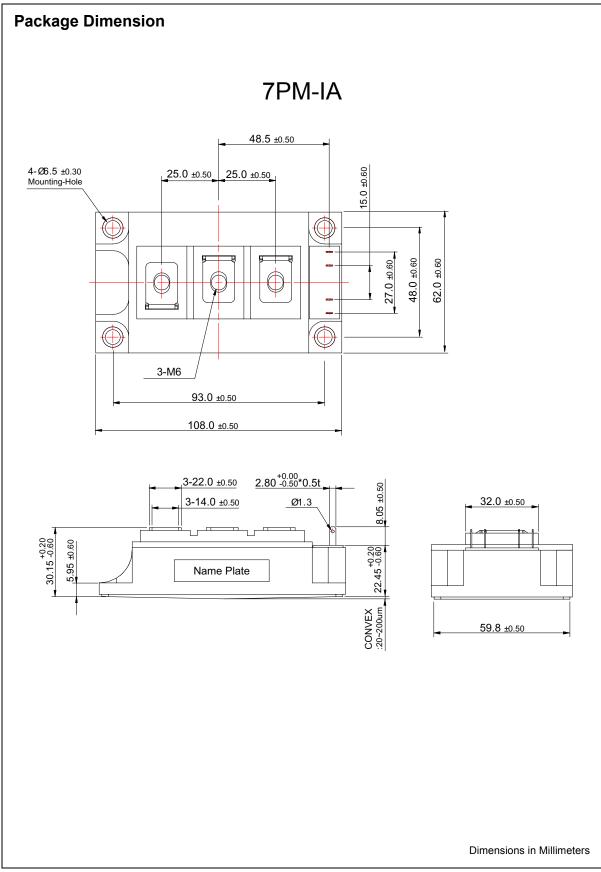


Fig 13. Reverse Recovery Characteristics(diode)



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